## DZSC.COM The RF Line **UHF Power Transistor**

... designed primarily for wideband, large-signal output and driver amplifier stages to 1.0 GHz.

- Designed for Class A Linear Power Amplifiers
- Specified 25 Volt, 900 MHz Characteristics: Output Power - 3.0 Watts Power Gain — 7.5 dB Min, Class AB
- WWW.DZSC.COM Gold Metallization for Improved Reliability



3.0 W, TO 1.0 GHz LINEAR UHF POWER TRANSISTOR NPN SILICON

# CASE 244-04, STYLE 1 (.280 SOE)

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	30	Vdc
Collector–Base Voltage	VCBO	60	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	29 0.167	Watts W/°C
Operating Junction Temperature	TJ	200	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

#### **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (T <sub>C</sub> = 70°C)	R <sub>θJC</sub>	6.0	°C/W
ELECTRICAL CHARACTERISTICS		B2	10.

#### **ELECTRICAL CHARACTERISTICS**

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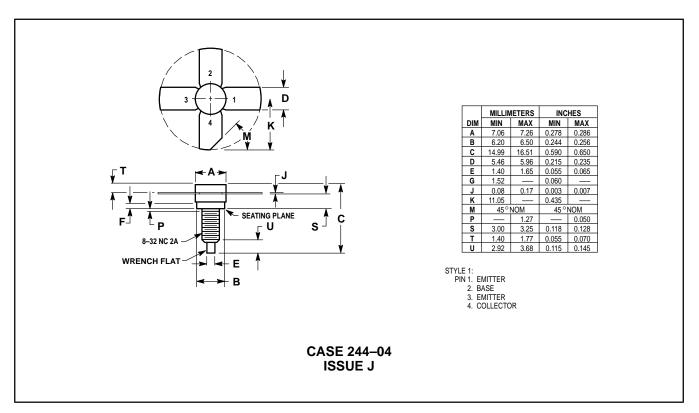
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	-N/8 1-3				
Collector–Emitter Breakdown Voltage $(I_C = 15 \text{ mA}, I_B = 0)$	V <sub>(BR)</sub> CEO	30	—	_	Vdc
Collector–Emitter Breakdown Voltage $(I_{C} = 15 \text{ mA}, V_{BE} = 0)$	V <sub>(BR)</sub> CES	60	—	_	Vdc
Collector-Base Breakdown Voltage ( $I_C = 15 \text{ mA}, I_E = 0$ )	V <sub>(BR)</sub> CBO	60	—		Vdc
Emitter–Base Breakdown Voltage ( $I_E = 5.0 \text{ mA}, I_C = 0$ )	V <sub>(BR)EBO</sub>	4.0	ina 7	TP-10	Vdc
Collector Cutoff Current ( $V_{CB} = 25 V, I_E = 0$ )	Сво	519	S WWW	2.0	mAdc
ON CHARACTERISTICS	510 2				
DC Current Gain (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 5.0 V)	hFE	20	—	80	
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 28 V, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	—	—	9.8	pF
FUNCTIONAL TESTS	•	•			•
Common–Emitter Amplifier Power Gain (V <sub>CE</sub> = 25 V, P <sub>out</sub> = 3.0 W, f = 900 MHz, I <sub>C</sub> = 0.4 A)	GPE	7.5	8.5	_	dB
Load Mismatch ( $V_{CE}$ = 25 V, I <sub>C</sub> = 0.4 A, P <sub>out</sub> = 3.0 W, f = 900 MHz, Load VSWR = $\infty$ :1, All Phase Angles)	Ψ	No Degradation in Output Power			



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#### PACKAGE DIMENSIONS



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